1. Scope :

This specification applies to silicon one-dimensional PSD chips,
Device No. PSD-00092-B.

2. Structure :

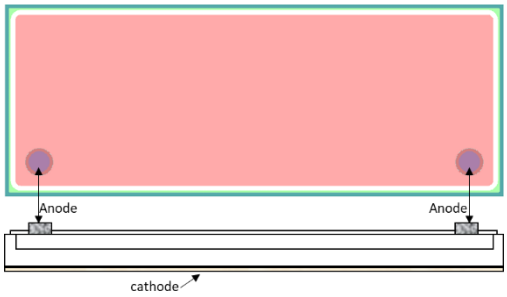
2-1. Planar type : PIN.
2-2. Electrodes :
Top side(Anode 1 & Anode 2) : Aluminum alloy.
Back side (Cathode) : Gold.

3. Size :

3-1. Chip size (including scribe lane) : 149.6 mils x 57.4 mils (3.8 mm x 1.46 mm).
3-2. Chip thickness : 12 ± 1.0 mils (0.305 ± 0.025 mm).
3-3. Active area : 143.3 mils x 51.1 mils (3.64 mm x 1.3 mm).
3-4. Bonding pad (Anode) : 7.87 ± 0.394 mils (0.20 ± 0.010 mm) Diameter
3-5. Pattern drawing : Refer to the attached drawing..

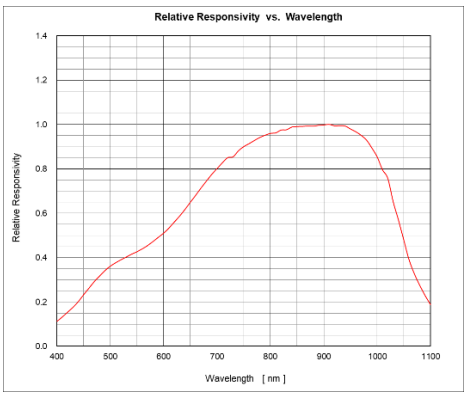
4. Electrical characteristics (Ta = 25 ℃)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
* Reverse dark current	I_D	VR=10V Ee=0mW/cm^2			10	nA
* Reverse breakdown voltage	$V_{(BR)R}$	IR=100uA Ee=0mW/cm^2	60			V
Reverse light current	I_L	VR =1V λp=940nm Ee=1mW/cm^2		26		μA
Junction Capacitance	C_J	VR= 1V f= 10KHz		20		pF
* Interelectrode Resistance	R_T	VR=0.1V	40		60	KΩ
Radiant Sensitivity	S_λ	λp=940nm		0.55		A/W
Spectral Response	SR		400 - 1100			nm



※Based on 100% probing

5. Relative spectral responsivity



※bare chip measured with integrating sphere, for reference only.